

Amendments to the Specification:

Please amend paragraph 24, which begins on page 8, as follows:

[0024] A problem with the semiconductor device 100 shown is that the insulating layers 112, 118a, 118b, 118c, and 124 are formed not only over[[in]] the second region 104 comprising the active areas 110 and other circuit components, but the insulating layers 112, 118a, 118b, 118c, and 124 are also formed over the first region 102 comprising the sensor 108. This is disadvantageous because when light 132 or other form of energy is directed toward the sensor 108, destructive interference 134 occurs within each of the insulating layers 112, 118a, 118b, 118c, and 124. As the light 132 passes through each of the insulating layers 112, 118a, 118b, 118c, and 124, more and more destructive interference 134 occurs, resulting in a reduction in the amount of light 132 sensed by the sensor 108. This results in decreased sensitivity of the sensor 108. Sensitivity is defined as the output signal in brightness subtracted by the output signal in darkness. Therefore, larger pixel sizes are required for the sensor 108 to accommodate for this decrease in sensitivity, in prior art designs.

Please amend paragraph 36, which begins on page 13, as follows:

[0036] Next, in accordance with preferred embodiments of the present invention, a plurality of apertures 240 is formed in the at least one first insulating layer, which includes IMD layers 218c, 218b, 218a, and ILD layer 212, as shown in Figure 3. The surface of the top IMD layer 218c may be exposed to a chemical-mechanical polish (CMP) process before the at least one first insulating layer 212, 218a[[218ac]], 218b, 218c is patterned.